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2SC5632G

Silicon NPN epitaxial planar type

For high-frequency amplification and switching

■ Features

- High transition frequency f_T
- S-Mini type package, allowing downsizing of the equipment and automatic insertion through the tape packing

Package

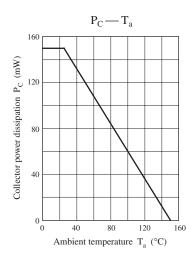
- Code SMini3-F2
- Marking Symbol; 2R

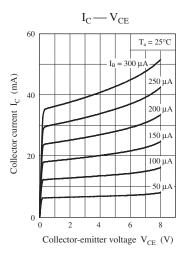
■ Absolute Maximum Ratings $T_a = 25$ °C

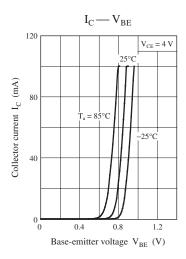
Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	V _{CBO}	15	V
Collector-emitter voltage (Base open)	V _{CEO}	8	V
Emitter-base voltage (Collector open)	V_{EBO}	3	S.V
Collector current	I_C	50	mA
Collector power dissipation	P _C	150	6W
Junction temperature	T_{j}	V0150 Q	°S
Storage temperature	T _{stg}	255 to +150	€6

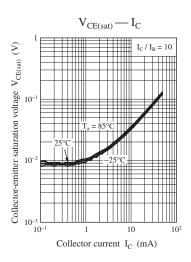
 S-Mini type package, allowing d and automatic insertion through t Absolute Maximum Ratings 	he tape pa	acking	SMini3 Markin Pin Na Base Emit Unit V V Markin Pin Na Call Ca	g Symb					
Parameter	Symbol	Rating	Unit	170)				
Collector-base voltage (Emitter open)	V _{CBO}	15	v v	o		s·			
Collector-emitter voltage (Base open)	V_{CEO}	8	v 0,012		ان در ا				
Emitter-base voltage (Collector open)	V_{EBO}	3	6.V 101 CO	(Silve				
Collector current	I_C	50	MAC VO	S					
Collector power dissipation	P _C	150	COW VO	yle .					
Junction temperature	T_{j}	V150 Q	<i>P3</i> ° (
Storage temperature	T _{stg}	255 to +150	166 O),						
Parameter Symbol Rating Unit Collector-base voltage (Emitter open) V _{CBO} 15 V Collector-emitter voltage (Base open) V _{CEO} 8 V Emitter-base voltage (Collector open) V _{EBO} 3 V Collector current I _C 50 mAC Collector power dissipation P _C MO GW Junction temperature T _{stg} 55 to +450 CC Storage temperature T _{stg} 55 to +450 CC Parameter Symbol Conditions Min Typ Max Unit									
Parameter. Other Calleston has a subtraction of the		10	Conditions	Min	Тур	Max	Unit V		
Collector-base voltage (Emitter open) V_{CBO} $V_{C} = 100 \text{p/A}$, $I_{E} = 0$ Emitter-base cutoff current (Collector open) I_{EBO} $V_{EB} = 2 \text{V}$, $I_{C} = 0$		15		2	·				
- · · · · · · · · · · · · · · · · · · ·			100		350	μΑ			
Forward current transfer ratio	h _{FE}			0.6		1.5			
h _{FE} ratio	Δh_{Fir}		= 4 V , $I_C = 100 \mu A$ = 4 V , $I_C = 2 \text{ mA}$	0.0		1.3	_		
Collector-enritter saturation voltage	V _{CE(sat)}	$V_{CE(sat)}$ $I_C = 20 \text{ mA}, I_B = 4 \text{ mA}$				0.1	V		
Transition frequency	f_T	$V_{CE} = 5 \text{ V}$	$I_{\rm C} = 15 \text{ mA}, f = 200 \text{ MHz}$	0.6	1.1		GHz		
Collector output capacitance (Common base, apput open circuited)	C _{ob}	$V_{CB} = 10$	$V, I_E = 0, f = 1 \text{ MHz}$		1.0	1.6	pF		

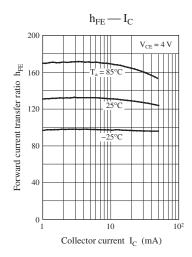
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors. 2. *: Δh_{FE} € h_{FE2} / h_{FE1}

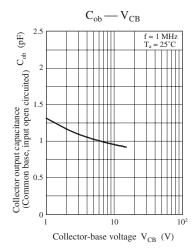






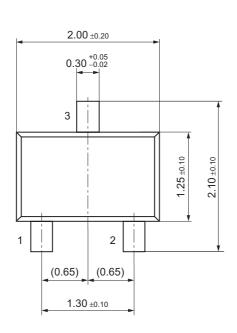


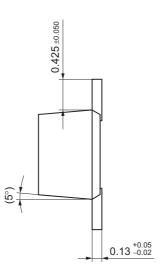




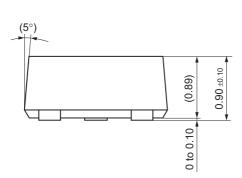
2 SJC00369AED

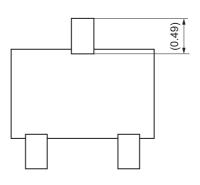
SMini3-F2 Unit: mm











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